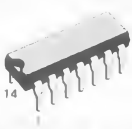
SGS-THOMSON MICROELECTRONICS

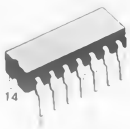
M54HC77
M74HC77

4-BIT D-TYPE LATCH

- HIGH SPEED
  t_{PD} = 15 ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION
  I_{CC} = 2 μA (MAX.) at T_A = 25°C
- HIGH NOISE IMMUNITY
  V_{NIH} = V_{NIL} = 28% V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|I_{OH}|$ = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  t_{PLH} = t_{PHL}
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE
  WITH 54/74LS77



B1N
Plastic Package



F1
Ceramic Frit Seal Package

M1
Micro Package

C1
Plastic Chip Carrier

ORDERING NUMBERS:

M54HC77 F1
M74HC77 B1N
M74HC77 F1
M74HC77 C1
M74HC77 M1

DESCRIPTION

The M54/74HC77 is a high speed CMOS 4-BIT D-TYPE LATCH fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.
It contains two groups of 2-bit latches controlled by an enable input (G1•2 or G3•4). These two latch groups can be used in different circuits.

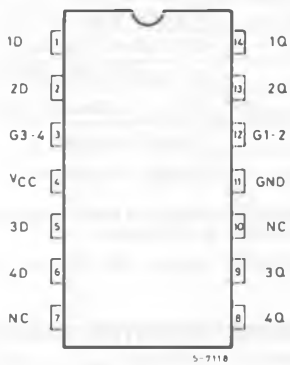
The data applied to the data inputs (1D, 2D, or 3D, 4D) are transfered to the Q outputs (1Q, 2Q, or 3Q, 4Q) respectively when the enable input (G1•2 or G3•4) is taken high. The Q outputs will follow the data inputs as long as the enable input is kept high. When the enable input is taken low, the information data applied to the data inputs is retained at the Q outputs. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

TRUTH TABLE

INPUTS		OUTPUT	FUNCTION
D	G	Q	
L	H	L	—
H	H	H	—
X	L	Q_n	LATCH

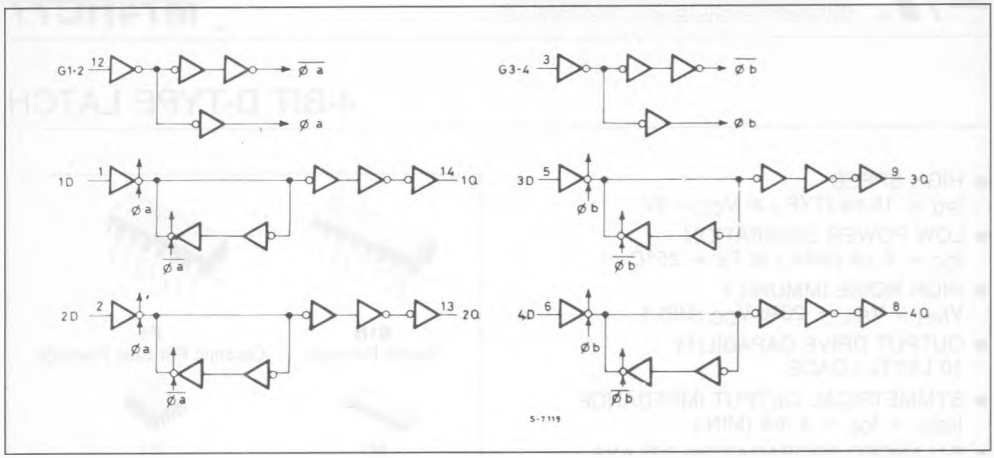
X: DON'T CARE

PIN CONNECTIONS (top view)



FOR CHIP CARRIER
INFORMATION CONTACT SGS-THOMSON

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	− 0.5 to 7	V
V_I	DC Input Voltage	− 0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	− 0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	− 65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≅ 65°C derate to 300 mW by 10 mW/°C: 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value		Unit
V_{CC}	Supply Voltage		2 to 6		V
V_I	Input Voltage		0 to V_{CC}		V
V_O	Output Voltage		0 to V_{CC}		V
T_A	Operating Temperature	74HC Series 54HC Series	− 40 to 85 − 55 to 125		°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V V_{CC} = 4.5V V_{CC} = 6 V	0 to 1000 0 to 500 0 to 400		ns

DC SPECIFICATIONS

Symbol	Parameter	V_{CC}	Test Condition		$T_A = 25°C$ 54HC and 74HC			−40 to 85°C 74HC		−55 to 125°C 54HC		Unit
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5	—	—	1.5	—	1.5	—	V
		4.5			3.15	—	—	3.15	—	3.15	—	
		6.0			4.2	—	—	4.2	—	4.2	—	
V_{IL}	Low Level Input Voltage	2.0			—	—	0.5	—	0.5	—	0.5	V
		4.5			—	—	1.35	—	1.35	—	1.35	
		6.0			—	—	1.8	—	1.8	—	1.8	
V_{OH}	High Level Output Voltage	2.0	V_I	I_O	1.9	2.0	—	1.9	—	1.9	—	V
		4.5	V_{IH} or V_{IL}	−20 μA	4.4	4.5	—	4.4	—	4.4	—	
		6.0			5.9	6.0	—	5.9	—	5.9	—	
		4.5		−4.0 mA	4.18	4.31	—	4.13	—	4.10	—	
		6.0		−5.2 mA	5.68	5.8	—	5.63	—	5.60	—	
V_{OL}	Low Level Output Voltage	2.0	V_{IH} or V_{IL}	20 μA	—	0	0.1	—	0.1	—	0.1	V
		4.5			—	0	0.1	—	0.1	—	0.1	
		6.0			—	0	0.1	—	0.1	—	0.1	
		4.5		4.0 mA	—	0.17	0.26	—	0.33	—	0.40	
		6.0		5.2 mA	—	0.18	0.26	—	0.33	—	0.40	
I_I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND		—	—	±0.1	—	±1	—	±1	μA
I_{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND		—	—	2	—	20	—	40	μA

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5V$, $T_A = 25°C$, $C_L = 15pF$, Input $t_r = t_f = 6ns$)

Symbol	Parameter	54HC and 74HC			Unit
		Min.	Typ.	Max.	
t_{TLH} t_{THL}	Output Transition Time		4	8	ns
t_{PLH} t_{PHL}	Propagation Delay Time (DATA-Q)		12	20	ns
t_{PLH} t_{PHL}	Propagation Delay Time (G-Q)		15	25	ns

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

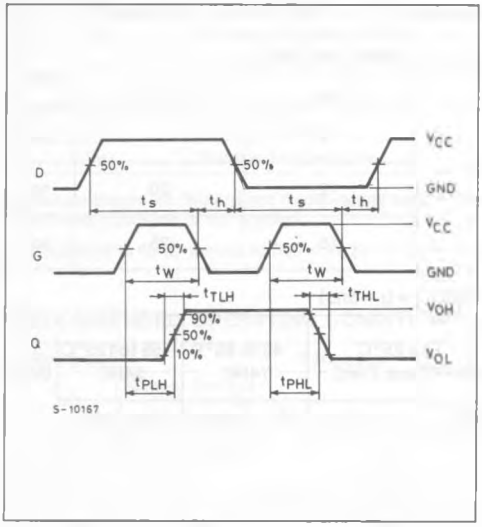
Symbol	Parameter	V_{CC}	Test Condition	$T_A = 25°C$ 54HC and 74HC			−40 to 85°C 74HC		−55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} T_{THL}	Output Transition Time	2.0		—	30	75	—	95	—	110	ns
		4.5		—	8	15	—	19	—	22	
		6.0		—	7	13	—	16	—	19	
t_{PLH} t_{PHL}	Propagation Delay Time (DATA-Q)	2.0		—	60	120	—	150	—	180	ns
		4.5		—	15	24	—	30	—	36	
		6.0		—	13	20	—	26	—	31	
t_{PLH} t_{PHL}	Propagation Delay Time (G-Q)	2.0		—	75	145	—	180	—	218	ns
		4.5		—	19	29	—	36	—	44	
		6.0		—	16	25	—	31	—	38	

AC ELECTRICAL CHARACTERISTICS (Continued)

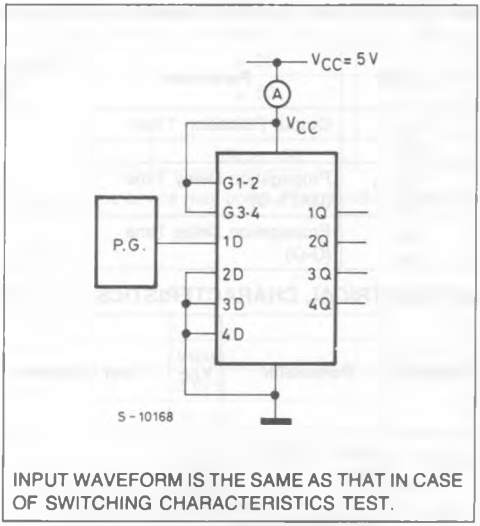
Symbol	Parameter	V_{CC}	Test Condition	T_A = 25°C 54HC and 74HC			− 40 to 85°C 74HC		− 55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
$t_{W(H)}$	Minimum Pulse Width (G)	2.0		—	30	75	—	95	—	110	ns
		4.5		—	8	15	—	19	—	22	
		6.0		—	7	13	—	16	—	19	
t_s	Minimum Set-Up Time	2.0		—	5	50	—	65	—	75	ns
		4.5		—	1	10	—	13	—	15	
		6.0		—	1	9	—	11	—	13	
t_h	Minimum Hold Time	2.0		—	—	25	—	30	—	40	ns
		4.5		—	—	5	—	6	—	8	
		6.0		—	—	5	—	6	—	7	
C_{IN}	Input Capacitance			—	5	10	—	10	—	10	pF
C_{PD} (*)	Power Dissipation Capacitance			—	27	—	—	—	—	—	pF

Note (*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load.

SWITCHING CHARACTERISTICS TEST WAVEFORM



TEST CIRCUIT I_{CC} (Opr.)



INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.